Philips Semiconductors

Product specification

Rectifier diodes Schottky barrier

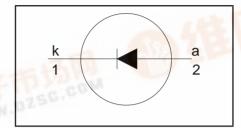
PBYL1025 series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

SYMBOL

WWW.DZ



QUICK REFERENCE DATA

$$V_R = 20 \text{ V}/25 \text{ V}$$

$$I_{F(AV)} = 10 \text{ A}$$

$$V_F \le 0.4 \text{ V}$$

GENERAL DESCRIPTION

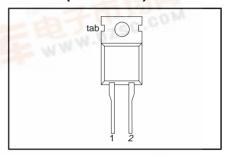
Schottky rectifier diodes intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYL1025 series is supplied in the SOD59 (TO220AC) conventional leaded package.

PINNING

PIN	DESCRIPTION		
1	cathode		
2	anode		
tab	cathode		

SOD59 (TO220AC)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
		PBYL10		20	25	
V_{RRM}	Peak repetitive reverse voltage		-	20	25	V
V_{RWM}	Working peak reverse voltage	13 m	-	20	25	V
V_R	Continuous reverse voltage	T _{mb} ≤ 119 °C	-	20	25	V
$I_{F(AV)}$	Average rectified forward current	square wave; $\delta = 0.5$; $T_{mb} \le 132$ °C	-	,	10	Α
I _{FRM}	Repetitive peak forward current	square wave; $\delta = 0.5$; $T_{mb} \le 132$ °C	-	2	20	А
I _{FSM}	Non-repetitive peak forward current	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$ pulse width and repetition rate			35 50	A A
I_{RRM}	Peak repetitive reverse surge current	pulse width and repetition rate limited by T _{i max}	-		1	Α
T_{j}	Operating junction temperature		-	1	50	°C
T_{stg}	Storage temperature	SC-CO	- 65	1	75	°C



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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance junction		-	-	3	K/W
R _{th j-a}	to mounting base Thermal resistance junction to ambient	in free air	-	60	-	K/W

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage	$I_{\rm F} = 10 \text{ A}; T_{\rm i} = 150^{\circ}\text{C}$	-	0.33	0.4	V
'		$I_{\rm F} = 10 \text{A}, T_{\rm i} = 125 ^{\circ} \text{C}$	-	0.39	0.45	V
		$I_{\rm F} = 20 \text{ A}$; $T_{\rm i} = 125 ^{\circ}\text{C}$	-	0.54	0.61	V
		$I_F = 20 \text{ A}$	-	0.57	0.64	V
I _R	Reverse current	$\dot{V}_R = V_{RWM}$	-	0.2	5	mΑ
		$V_{R} = V_{RWM}$; $T_{i} = 100^{\circ}C$	-	15	30	mΑ
C _d	Junction capacitance	$V_R = V_{RWM}^{COMM}$; $T_j = 100^{\circ}C$ $V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_j = 25^{\circ}C$ to $125^{\circ}C$	-	580	-	pF

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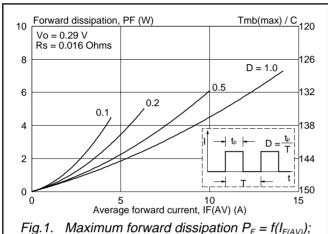
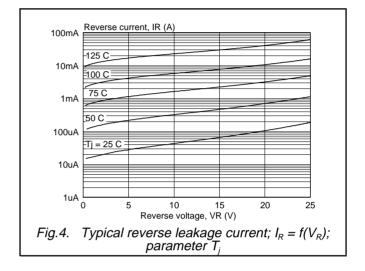


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)});$ square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}.$



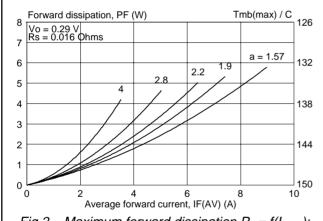
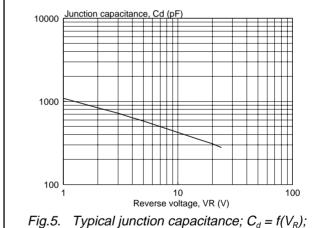


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)});$ square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}.$



Typical junction capacitance; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25^{\circ}\text{C}$ to 125°C .

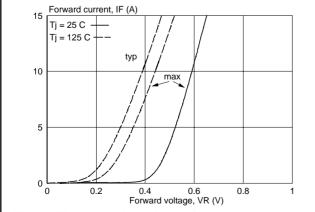


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

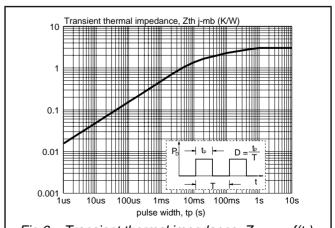
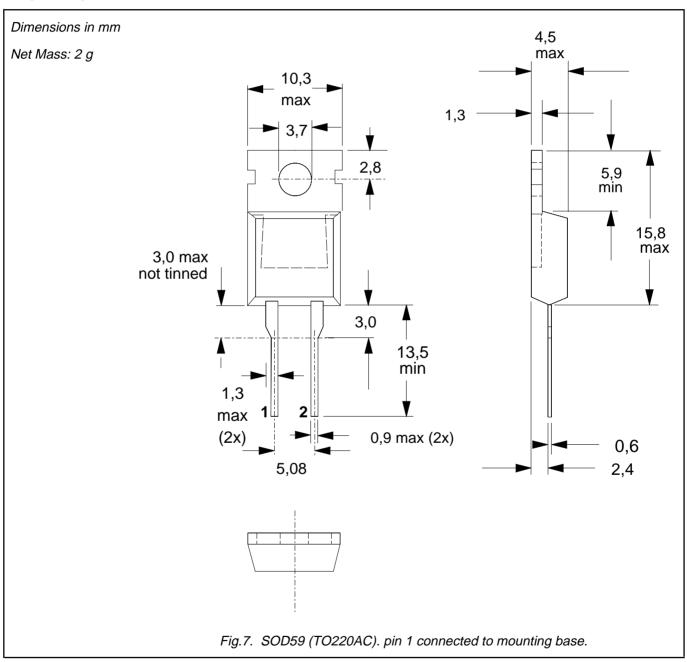


Fig.6. Transient thermal impedance; $Z_{th j-mb} = f(t_p)$.

Rectifier diodes Schottky barrier PBYL1025 series

MECHANICAL DATA



- Refer to mounting instructions for TO220 envelopes.
 Epoxy meets UL94 V0 at 1/8".

Rectifier	diodes
Schottky	barrier

PBYL1025 series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification This data sheet contains preliminary data; supplementary data may be published later				
Product specification This data sheet contains final product specifications.				
Limiting values				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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